



	Experiment title: In-situ real-time GI-SAXS/WAXS investigation of diindenoperylene orientation and growth kinetics on monolayer MoS ₂	Experiment number: SC-4814
Beamline: ID10	Date of experiment: from: 02.03.2018 to: 06.03.2018	Date of report: 3.3.2020
Shifts: 12	Local contact(s): Andrei Chumakov	<i>Received at ESRF:</i>
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Report:

1. Abstract

During this beamtime we performed in-situ real-time GI-SAXS/WAXS experiments of diindenoperylene (DIP) growing on monolayer MoS₂ and few-layer MoS₂ with different alignment of atomic layers [1]. We studied the intra-island molecular orientation of the DIP molecules during growth on MoS₂ with different alignment. In-situ real-time GIWAXS was employed to verify the *lying-down* or *standing-up* DIP phase in thin film [2].

2. Experimental Results

Our setup consisted of organic molecular beam deposition (OMBD) chamber [3] and 2D detector: Pilatus in 0.36m sample-detector distance to record GIWAXS data. We deposited in total eight samples with different substrates and substrate temperatures. In real-time GIWAXS measurements we tracked the 001 integral intensity and diffraction peak width along q_z and q_{xy} directions in reciprocal space maps (RSMs). The total deposition time was 90 minutes with the integration time of 60 s for single frame. The fitted change of unit cell's c axis as a function of effective thickness (nm) for *lying-down* and *standing-up* DIP are given in Fig. 2. We found out that the orientation of the MoS₂ layers subsequently influences the orientation of DIP molecules. Fig. 1 shows the 001 diffraction peak positions of DIP layers ($q \approx 0.39 \text{ \AA}^{-1}$) grown on 3 and 9 nm thick MoS₂ films (left and right RSM). On the horizontally aligned MoS₂, we also detected the 110 diffraction peak ($q \approx 1.15 \text{ \AA}^{-1}$), see Fig. 1 (left). More diffraction spots were

observed for DIP thin films on a MoS₂ monolayer, which were used to calculate the full set of unit cell parameters and the molecular orientation within the unit cell.

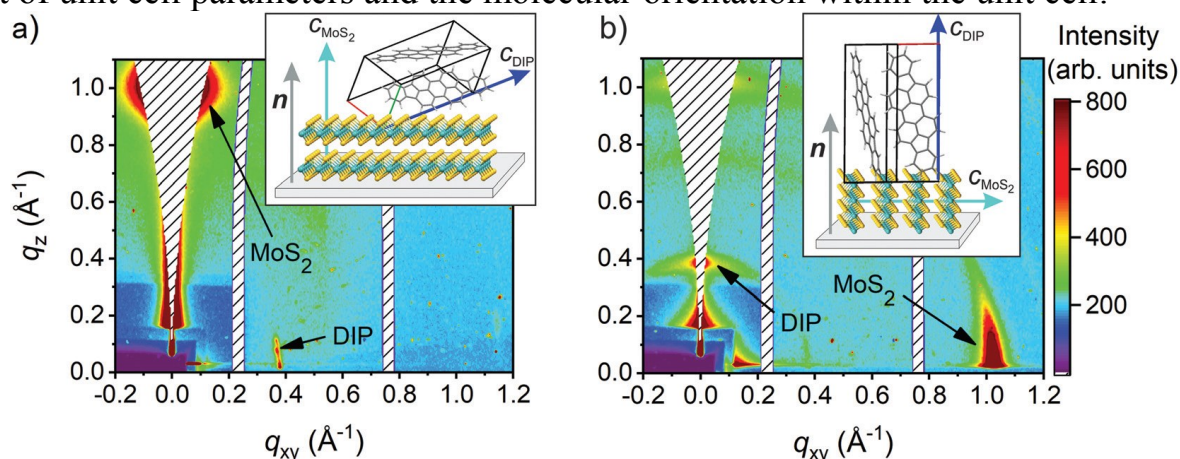


Fig. 1 reciprocal space maps of MoS₂ with different alignment and deposited DIP layers. Inset shows schematic of mutual orientations of the c-axes of DIP and MoS₂

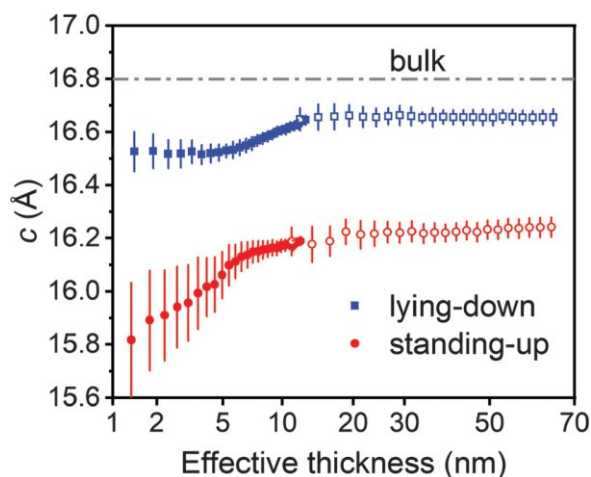


Fig. 2 Temporal evolution of unit cell's *c* axis as a function of effective thickness (nm) for *lying-down* and *standing-up* DIP

3. Remarks on quality of measurements

We found the ID10 beamline particularly suited for our in-situ real-time GI-SAXS/WAXS experiments with weakly scattering organic materials. Although we had to take some precautions in order to avoid beam damage on our samples, we consider the obtained signal very good.

4. Status and progress of data evaluation

We fully analyzed the data and published two articles out of this experiment.

- N. Mrkyvkova *et al.*, Appl. Phys. Lett. 114 (2019), 251906

- J. Hagara *et al.*, Phys. Chem. Chem. Phys. 22 (2020), 3097-3104

We thank O. Konovalov for the valuable support and Andrei Chumakov for local contact during the beamtime.

5. References

1. M. Sojkova *et al.*, RSC Adv. 9 (2019), 29645-29651
2. M. Hodas *et al.*, ACS Appl. Nano Mater. 1 (2018), 2819-2826
3. K. A. Ritley *et al.*, Rev. Sci. Instr. 72 (2000), 1453